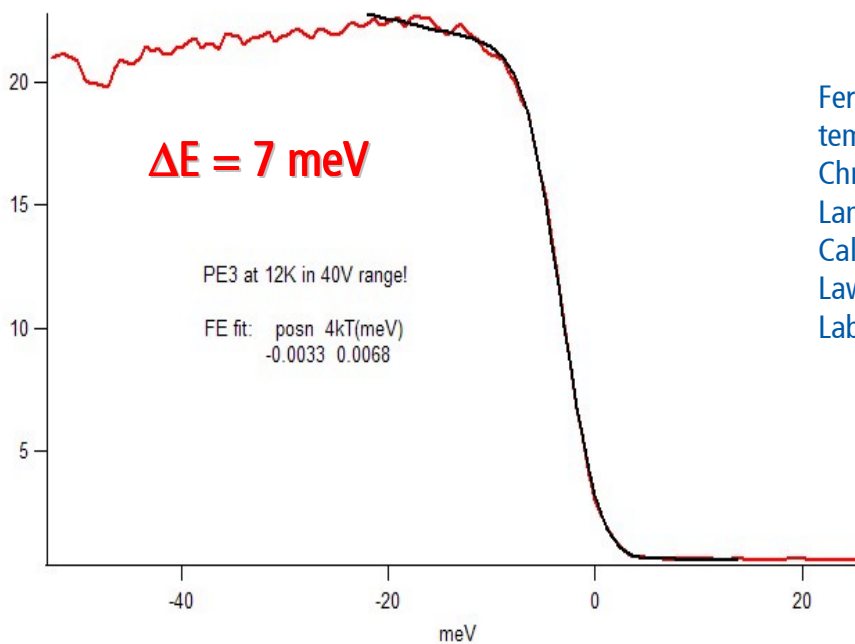


# Fermi-edge of a single crystal TiTe<sub>2</sub> sample at low temperature (PHOIBOS 150)

## Application Notes

The Fermi-edge of a single crystal TiTe<sub>2</sub> sample was measured at low temperature. The diode closest to the sample read 12 K. A sample temperature of 17 K was estimated. The data was taken with a PHOIBOS 150 CCD analyzer at 3 eV pass energy and with 0.2 mm slit width.



Fermi-edge of TiTe<sub>2</sub> at low temperatures. Data courtesy Chris Jozwiak and Alessandra Lanzara (University of California at Berkeley and Lawrence Berkeley National Laboratory).

The Fermi edge of a cold metallic solid is a good testing ground for the analyzer resolution. The Fermi-Dirac distribution gives the fractional distribution of levels at a finite temperature:

$$F(E) = \frac{1}{e^{\frac{E-E_F}{kT}+1}}$$

where  $E_F$  is the Fermi energy,  $T$  the temperature, and  $k$  is the Boltzmann constant ( $k=1/11600$  eV/K). According to the Fermi-Dirac statistics a width of  $\Delta E = 4 \cdot k \cdot T = 6$  meV is expected at  $T = 17$ K.

At  $E_p = 3$  eV with a 0.2 mm slit the contribution of the PHOIBOS analyzer  $\Delta E_A$  to the total line width of about 4 meV is calculated from:

$$\begin{aligned} \Delta E_A &= \left( \frac{s_1 + s_2}{4R_0} + \frac{\alpha^2}{4} \right) E_p \\ &= \frac{s_1 + s_2}{2R_0} E_p = \frac{s_1}{R_0} E_p \\ &= \frac{0.2 \text{ mm}}{150 \text{ mm}} \cdot 3 \text{ eV} \\ &= \mathbf{4 \text{ meV}} \end{aligned}$$

is confirmed by the deconvolution  $7^2 - 6^2 \approx 4^2$  of the experimental data: 4 meV

Here,  $s_1$ ,  $s_2$ ,  $R_0$ ,  $\alpha$  and  $E_p$  are the width of the entrance slit, the width of the exit slit, the mean radius of the analyzer, and the pass energy, respectively.

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